

BAV756DW SWITCHING DIODE

FEATURES

Power dissipation

$$P_D: 200 \text{ mW (} T_{amb}=25^\circ\text{C)}$$

Collector current

$$I_F: 150 \text{ mA}$$

Collector-base voltage

$$V_R: 75 \text{ V}$$

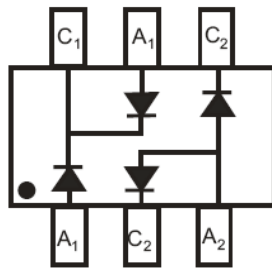
Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOT-363



MARKING:KCA



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=2.5\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R=75\text{V}$ $V_R=20\text{V}$		2.5 0.025	μA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Junction capacitance	C_j	$V_R=0\text{V}$ $f=1\text{MHz}$		2	pF
Reveres recovery time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1I_R$ $R_L=100\Omega$		4	nS

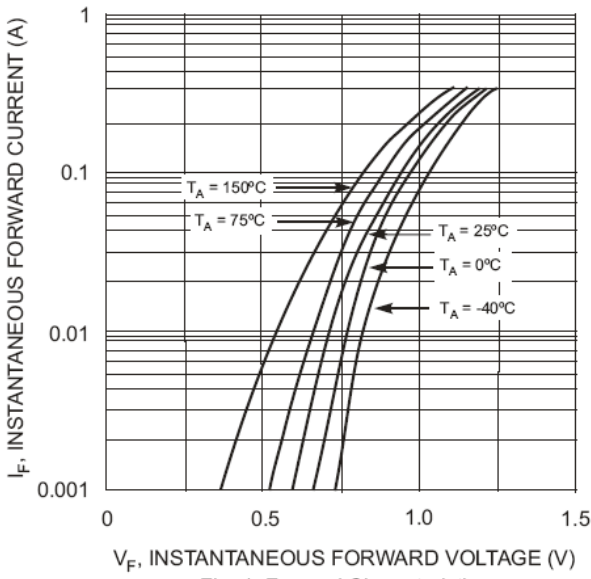


Fig. 1 Forward Characteristics

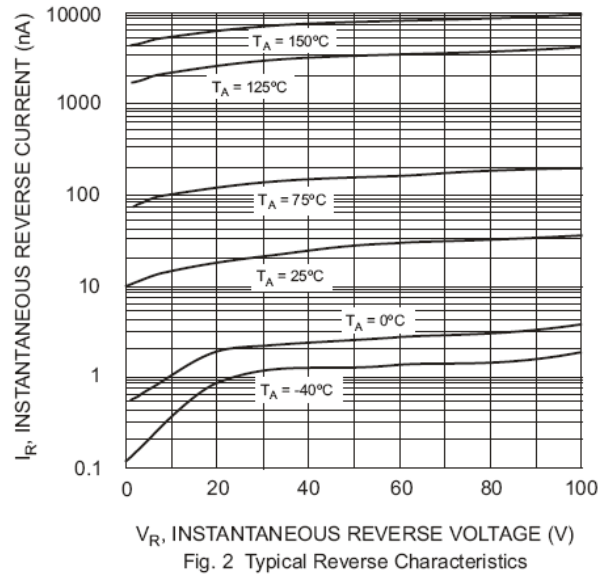


Fig. 2 Typical Reverse Characteristics

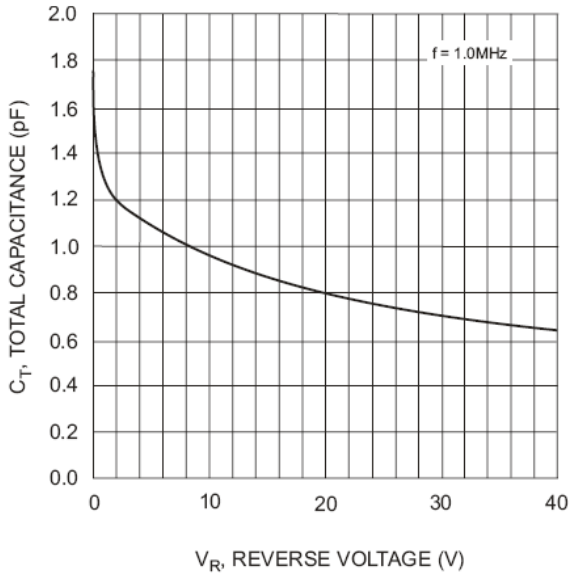


Fig. 3 Typical Capacitance vs. Reverse Voltage

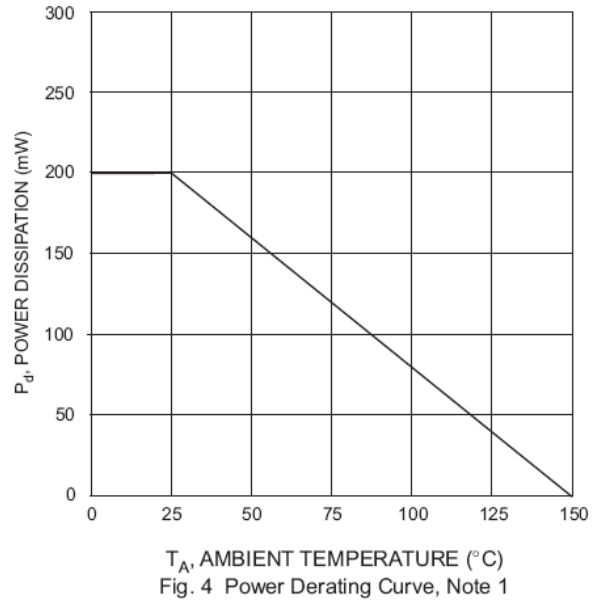


Fig. 4 Power Derating Curve, Note 1